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(54) **CAPACITOR CONSTRUCTIONS, SEMICONDUCTOR CONSTRUCTIONS, AND METHODS OF FORMING ELECTRICAL CONTACTS AND SEMICONDUCTOR CONSTRUCTIONS**

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(\* ) Notice: Subject to any disclaimer, the term of this patent is extended or adjusted under 35 U.S.C. 154(b) by 0 days.

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(58) **Field of Classification Search** ..... **438/244, 438/253-256, 387, 391, 396-399; 257/296**  
See application file for complete search history.

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(57) **ABSTRACT**

The invention includes a method of forming a semiconductor construction. A semiconductor substrate is provided, and a conductive node is formed to be supported by the semiconductor substrate. A first conductive material is formed over the conductive node and shaped as a container. The container has an opening extending therein and an upper surface proximate the opening. The container opening is at least partially filled with an insulative material. A second conductive material is formed over the at least partially filled container opening and physically against the upper surface of the container. The invention also includes semiconductor structures.

**21 Claims, 6 Drawing Sheets**

